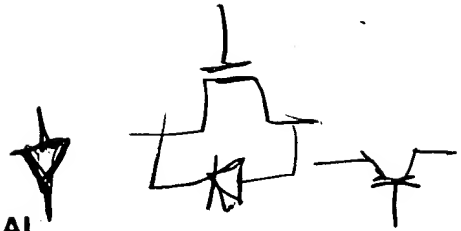


**APPENDIX A  
CLAIMS INVOLVED IN THE APPEAL**



1. (original) A temperature-protected semiconductor switch,  
5 comprising:  
a semiconductor body of first conductivity type;  
a semiconductor switch element formed of a plurality of cells connected  
in parallel and including an integrated reverse diode;  
a temperature sensor which generates a first signal given the  
10 occurrence of an excess temperature, wherein the  
semiconductor switch element and the temperature sensor are  
integrated together in the semiconductor body; and  
a charge carrier detector that generates a second signal given the  
occurrence of free charge carriers in the semiconductor body.
- 15 2. (original) A temperature-protected semiconductor switch as claimed  
in claim 1, further comprising:  
a parasitic component formed between the charge carrier detector, the  
semiconductor body and at least one cell of the semiconductor  
20 switch element.
3. (original) A temperature-protected semiconductor switch as claimed  
in claim 1, further comprising:  
in evaluation means, wherein the first and second signals are supplied  
25 to the evaluation means and logically operated with one another  
thereat for indicating an unambiguous excess temperature in the  
semiconductor switch element.
4. (original) A temperature-protected semiconductor switch as claimed  
30 in claim 1, wherein the charge carrier detector is positioned adjacent the  
temperature sensor.

5. (original) A temperature-protected semiconductor switch as claimed in claim 1, wherein the temperature sensor is attached proximate a hottest location of the semiconductor body

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6. (original) A temperature-protected semiconductor switch as claimed in claim 1, wherein the charge carrier detector is positioned adjacent a signal line of the temperature sensor leading out of the semiconductor switch.

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7. (original) A temperature-protected semiconductor switch as claimed in claim 3, wherein the evaluation means is monolithically integrated with the semiconductor switch.

8. (original) A temperature-protected semiconductor switch as claimed in claim 1, further comprising:

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at least one of a bipolar transistor and a thyristor as the temperature sensor.

9. (original) A temperature-protected semiconductor switch as claimed in claim 1, wherein the first conductivity type is n-conductive.

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